



Memory

Prof. Kavita Bala and Prof. Hakim Weatherspoon CS 3410, Spring 2014

Computer Science

Cornell University

See P&H Appendix B.8 (register files) and B.9

Administrivia

Make sure to go to *your* Lab Section this week
Completed Lab1 due *before* winter break, Friday, Feb 14th
Note, a <u>Design Document</u> is due when you submit Lab1 final circuit
Work **alone**

Save your work!

- Save often. Verify file is non-zero. Periodically save to Dropbox, email.
- Beware of MacOSX 10.5 (leopard) and 10.6 (snow-leopard)

Homework1 is out

Due a week before prelim1, Monday, February 24th

Work on problems incrementally, as we cover them in lecture (i.e. part 1,

Office Hours for help

Work alone

Work alone, **BUT** use your resources

- Lab Section, Piazza.com, Office Hours
- Class notes, book, Sections, CSUGLab

Administrivia

Check online syllabus/schedule

http://www.cs.cornell.edu/Courses/CS3410/2014sp/schedule.html

Slides and Reading for lectures

Office Hours

Homework and Programming Assignments

Prelims (in evenings):

- Tuesday, March 4th
- Thursday, May 1th

Schedule is subject to change

Collaboration, Late, Re-grading Policies

"Black Board" Collaboration Policy

- Can discuss approach together on a "black board"
- Leave and write up solution independently
- Do not copy solutions

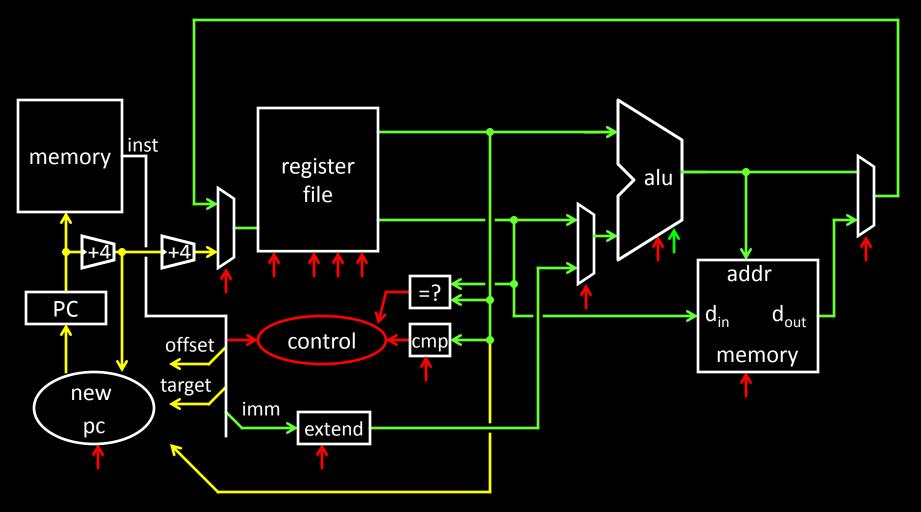
Late Policy

- Each person has a total of four "slip days"
- Max of two slip days for any individual assignment
- Slip days deducted first for any late assignment, cannot selectively apply slip days
- For projects, slip days are deducted from all partners
- 25% deducted per day late after slip days are exhausted

Regrade policy

- Submit written request to lead TA,
 and lead TA will pick a different grader
- Submit another written request, lead TA will regrade directly
- Submit yet another written request for professor to regrade.

Big Picture: Building a Processor



A Single cycle processor

Goals for today

Review

Finite State Machines

Memory

- Register Files
- Tri-state devices
- SRAM (Static RAM—random access memory)
- DRAM (Dynamic RAM)

Which statement(s) is true

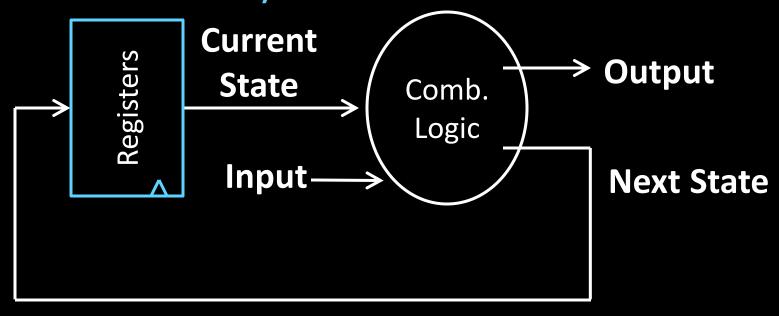
- (A) In a Moore Machine output depends on both current state and input
- (B) In a Mealy Machine output depends on current state and input
- (C) In a Mealy Machine output depends on next state and input
- (D) All the above are true
- (E) None are true

Which statement(s) is true

- (A) In a Moore Machine output depends on both current state and input
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- (D) All the above are true
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Mealy Machine

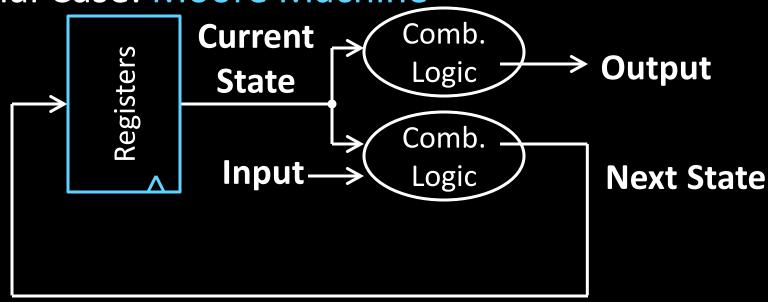
General Case: Mealy Machine



Outputs and next state depend on both current state and input

Moore Machine

Special Case: Moore Machine



Outputs depend only on current state

Example: Digital Door Lock



Digital Door Lock

Inputs:

- keycodes from keypad
- clock

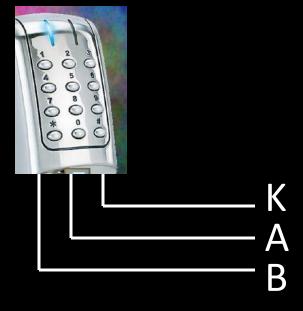
Outputs:

- "unlock" signal
- display how many keys pressed so far

Door Lock: Inputs

Assumptions:

- signals are synchronized to clock
- Password is B-A-B

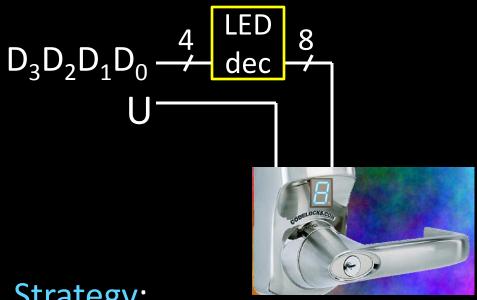


K	A	В	Meaning			
0	0	0	Ø (no key)			
1	1	0	'A' pressed			
1	0	1	'B' pressed			

Door Lock: Outputs

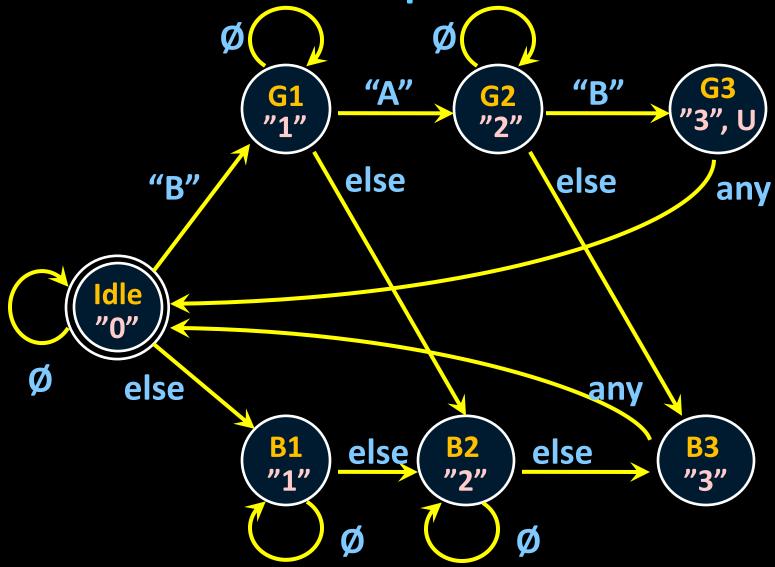
Assumptions:

High pulse on U unlocks door

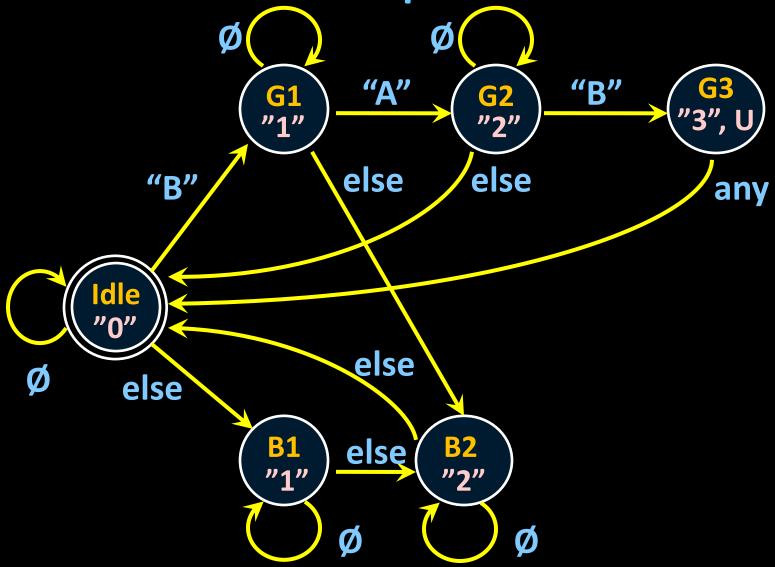


Strategy:

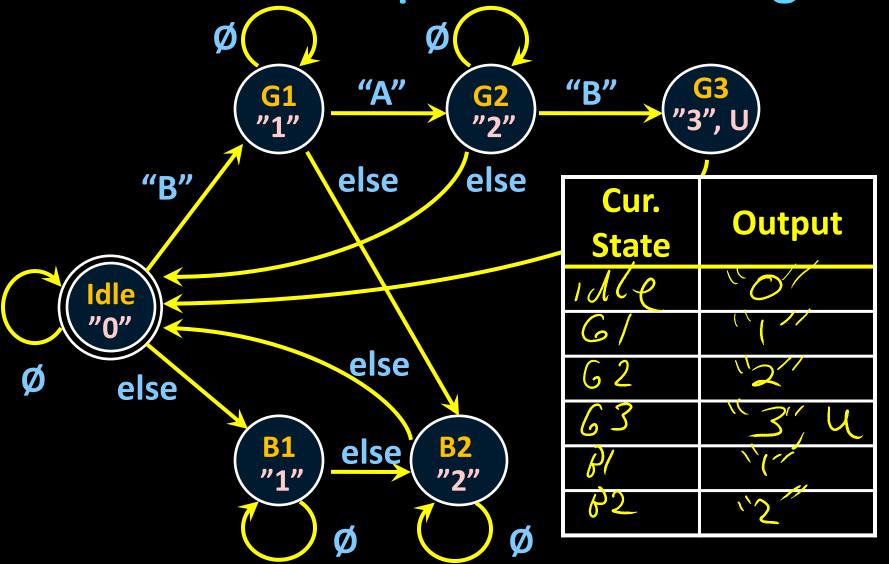
- (1) Draw a state diagram (e.g. Moore Machine)
- (2) Write output and next-state tables
- (3) Encode states, inputs, and outputs as bits
- (4) Determine logic equations for next state and outputs

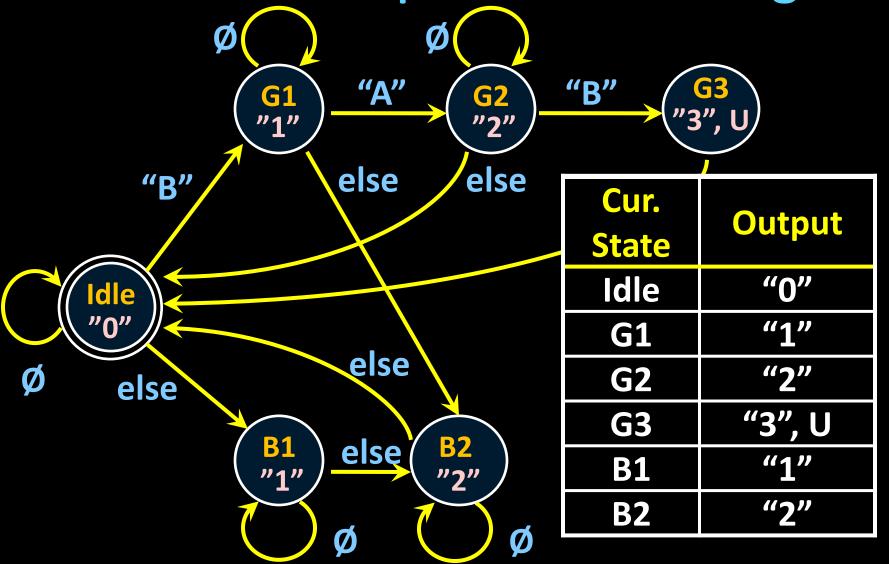


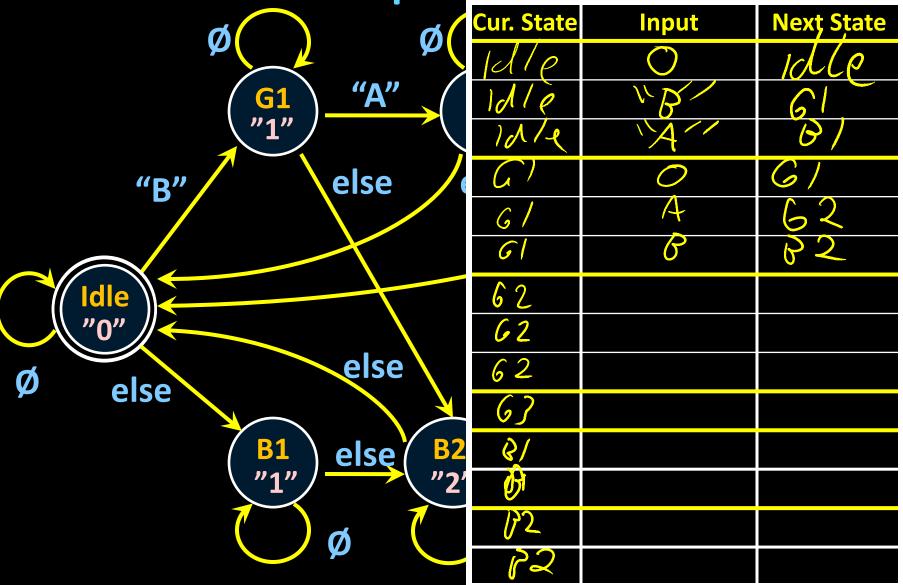
(1) Draw a state diagram (e.g. Moore Machine)



(1) Draw a state diagram (e.g. Moore Machine)







\emptyset \emptyset	Cur. State	Input	Next State
	Idle	Ø	Idle
G1 "A"	Idle	"B"	G1
"1"	Idle	"A"	B1
"B" else	G1	Ø	G1
	G1	"A"	G2
	G1	"B"	B2
Idle	G2	Ø	B2
"0" ★	G2	"B"	G3
Ø else	G2	"A"	Idle
P Else	G3	any	Idle
(B1) else (B2)	B1	Ø	B1
"1"	B1	K	B2
	B2	Ø	B2
	B2	K	Idle

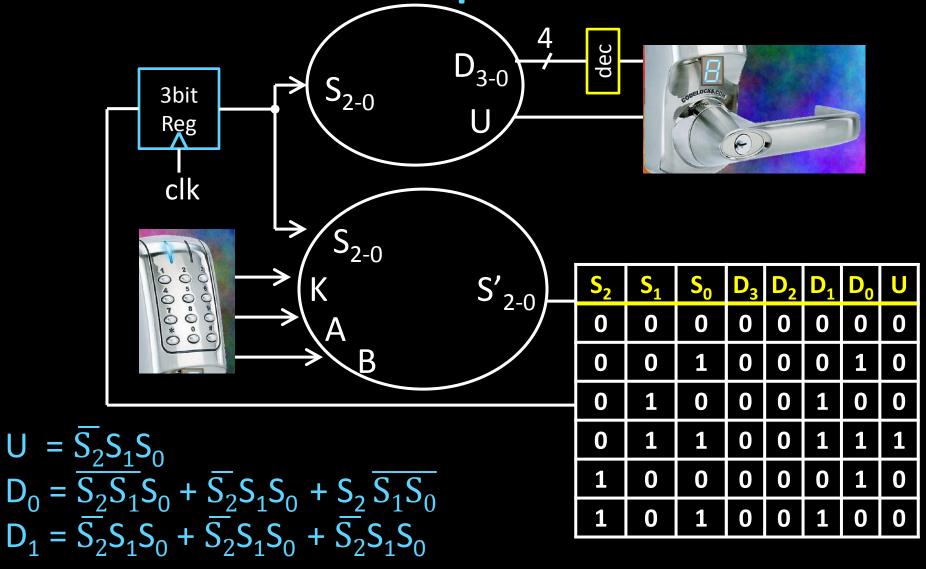
State Table Encoding

S ₂	S ₁	S ₀	D_3	D_2	D_1	D_0	U
0	0	0	0	0	0	0	0
0	0	1	0	0	0	1	0
0	1	0	0	0	1	0	0
0	1	1	0	0	1	1	1
1	0	0	0	0	0	1	0
1	0	1	0	0	1	0	0

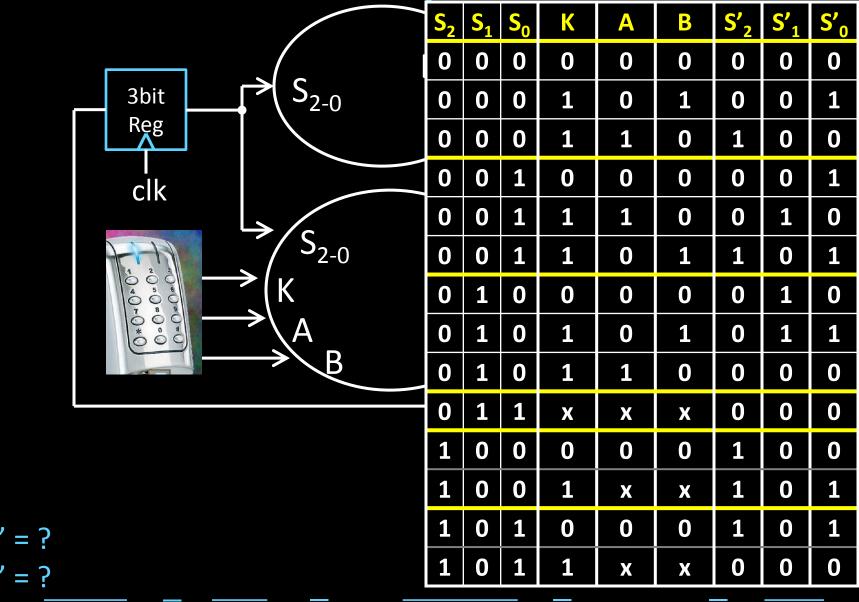
	State	S ₂	S ₁	S ₀
3 L	Idle	0	0	0
	G1	0	0	1
	G2	0	1	0
	G3	0	1	1
	B1	1	0	0
(B2	1	0	1

S ₂	S ₁	S ₀	K	A	В	S',	S' ₁	S' ₀
							_	
0	0	0	0	0	0	0	0	0
0	0	0	1	0	1	0	0	1
0	0	0	1	1	0	1	0	0
0	0	1	0	0	0	0	0	1
0	0	1	1	1	0	0	1	0
0	0	1	1	0	1	1	0	1
0	1	0	0	0	0	0	1	0
0	1	0	1	0	1	0	1	1
0	1	0	1	1	0	0	0	0
0	1	1	X	х	Х	0	0	0
1	0	0	0	0	0	1	0	0
1	0	0	1	х	х	1	0	1
1	0	1	0	0	0	1	0	1
1	0	1	1	Х	Х	0	0	0

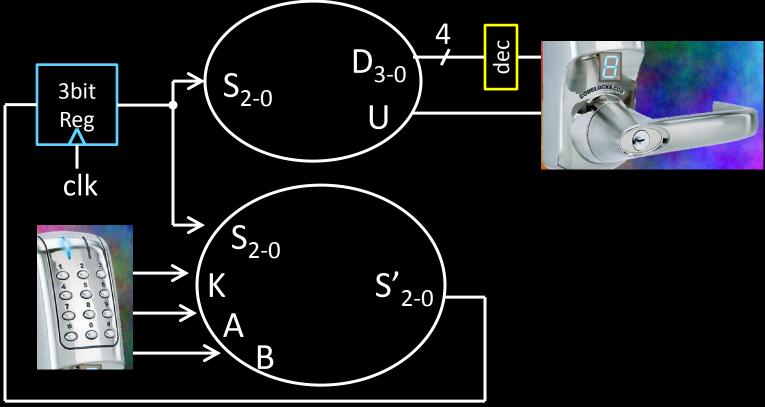
ts, and outputs as bits



(4) Determine logic equations for next state and outputs

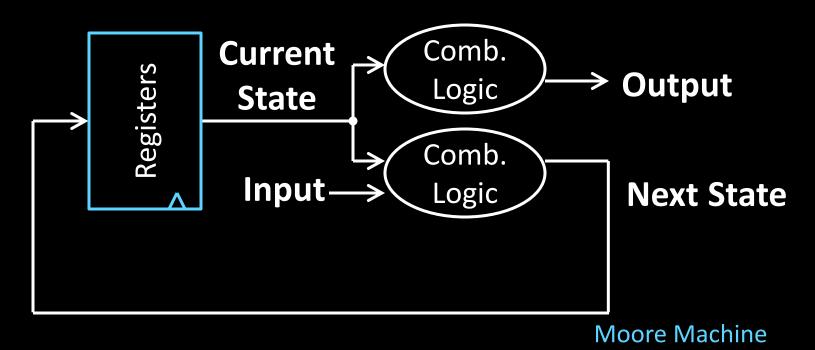


 $S_2' = \overline{S_2S_1S_0}KA\overline{B} + \overline{S_2S_1}S_0K\overline{A}B + S_2\overline{S_1S_2KAB} + \overline{S_2}S_1S_0K + S_2\overline{S_1}S_0\overline{KAB}$



Strategy:

- (1) Draw a state diagram (e.g. Moore Machine)
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Strategy:

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Finite State Machines

Memory

- CPU: Register Files (i.e. Memory w/in the CPU)
- Scaling Memory: Tri-state devices
- Cache: SRAM (Static RAM—random access memory)
- Memory: DRAM (Dynamic RAM)

Goal:

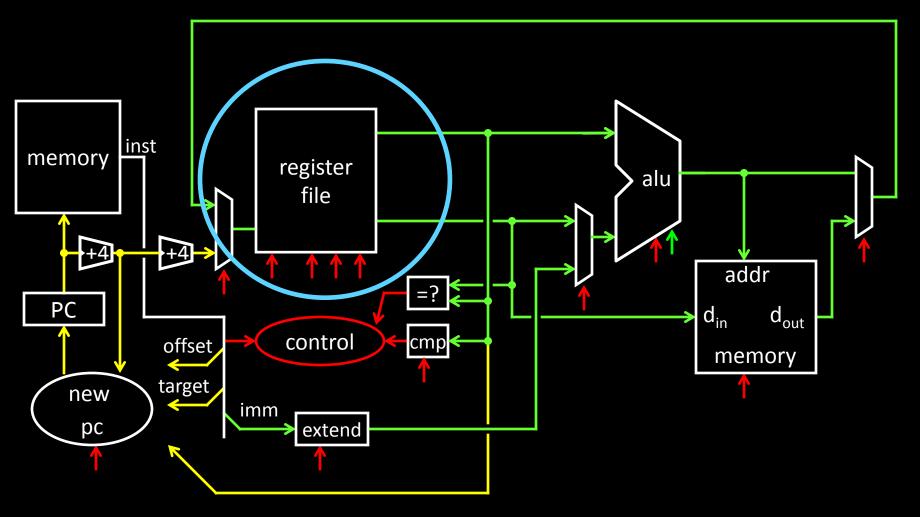
How do we store results from ALU computations?

How do we use stored results in subsequent operations?

Register File

How does a Register File work? How do we design it?

Big Picture: Building a Processor

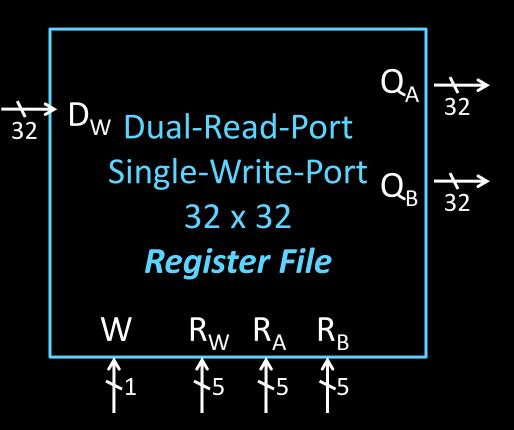


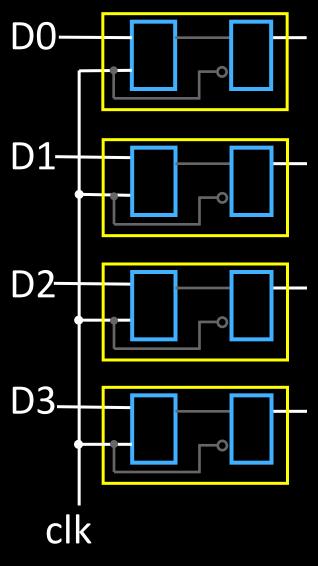
A Single cycle processor

Register File

N read/write registers

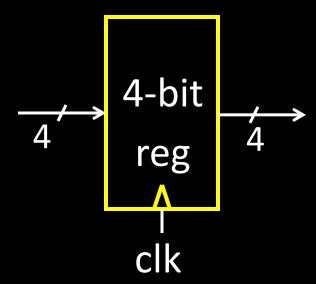
Indexed by register number





Recall: Register

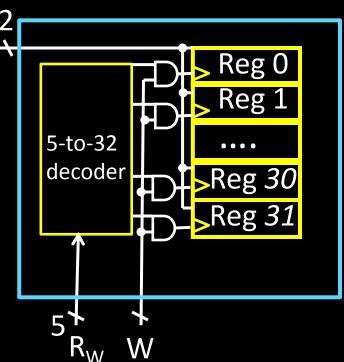
- D flip-flops in parallel
- shared clock
- extra clocked inputs:write_enable, reset, ...



Register File

N read/write registers

 Indexed by register number



How to write to one register in the register file?

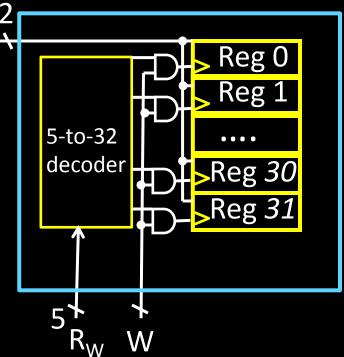
Need a decoder

Activity# write truth table for 3-to-8 decoder

Register File

N read/write registers

 Indexed by register number



How to write to one register in the register file?

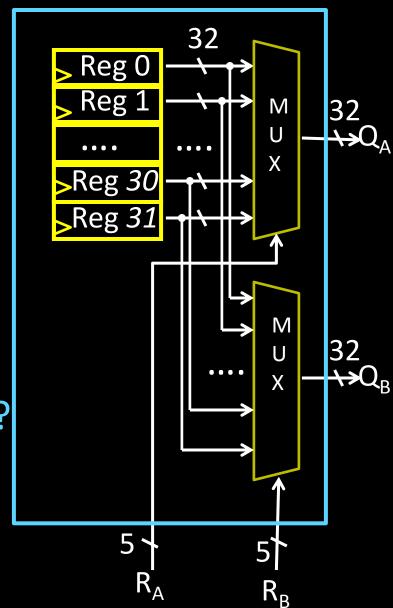
Need a decoder

Register File

- N read/write registers
- Indexed by register number

How to read from two registers?

Need a multiplexor

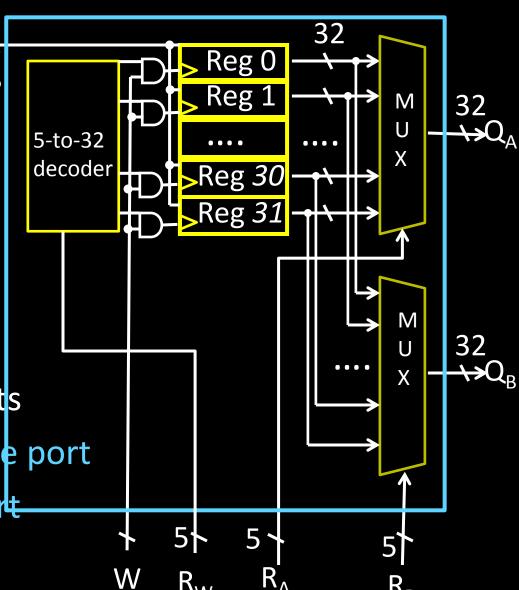


Register File

- N read/write registers
- Indexed by register number

Implementation:

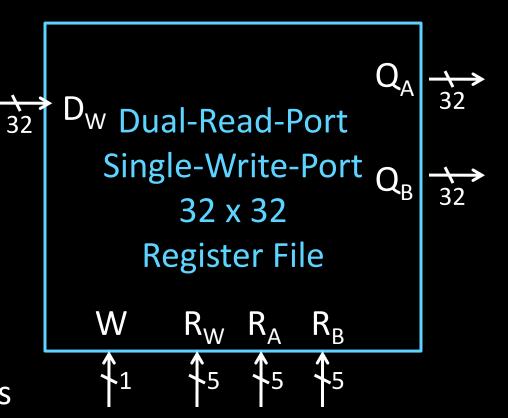
- D flip flops to store bits
- Decoder for each write port
- Mux for each read port



Register File

N read/write registers

Indexed by register number



Implementation:

- D flip flops to store bits
- Decoder for each write port
- Mux for each read port

Register File

- N read/write registers
- Indexed by register number

What happens if same register read and written during same clock cycle?

Implementation:

- D flip flops to store bits
- Decoder for each write port
- Mux for each read port

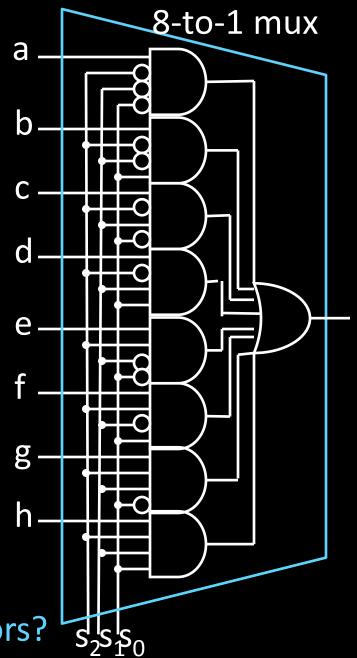
Tradeoffs

Register File tradeoffs

- + Very fast (a few gate delays for both read and write)
- + Adding extra ports is straightforward
- Doesn't scale
 e.g. 32Mb register file with
 32 bit registers
 Need 32x 1M-to-1 multiplexor

and 32x 20-to-1M decoder

How many logic gates/transistors?



Takeway

Register files are very fast storage (only a few gate delays), but does not scale to large memory sizes.

Goals for today

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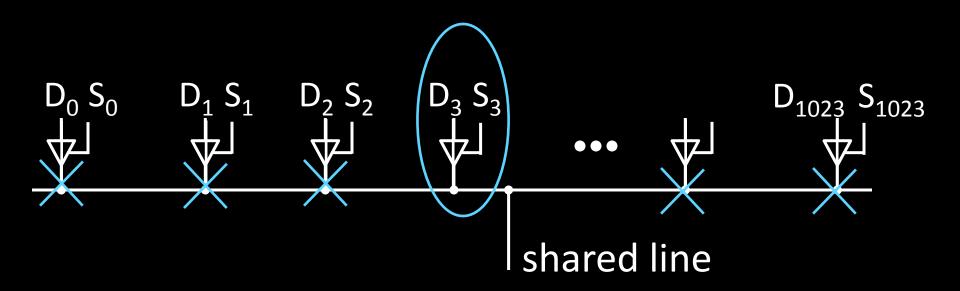
Next Goal

How do we scale/build larger memories?

Building Large Memories

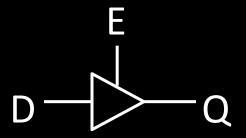
Need a shared bus (or shared bit line)

- Many FlipFlops/outputs/etc. connected to single wire
- Only one output drives the bus at a time



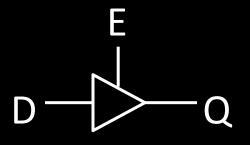
How do we build such a device?

- If enabled (E=1), then Q=D
- Otherwise, Q is not connected (z = high impedance)

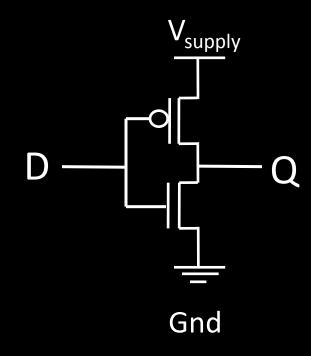


ш	D	Q
0	0	Z
0	1	Z
1	0	0
1	1	1

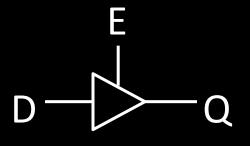
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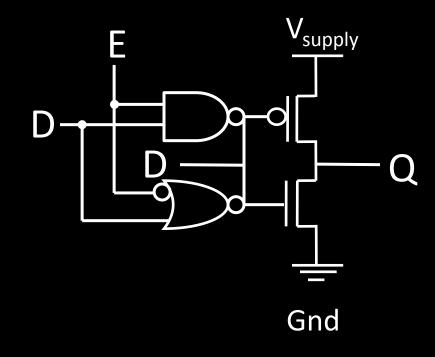
Ε	D	Q
0	0	Z
0	1	Z
1	0	0
1	1	1



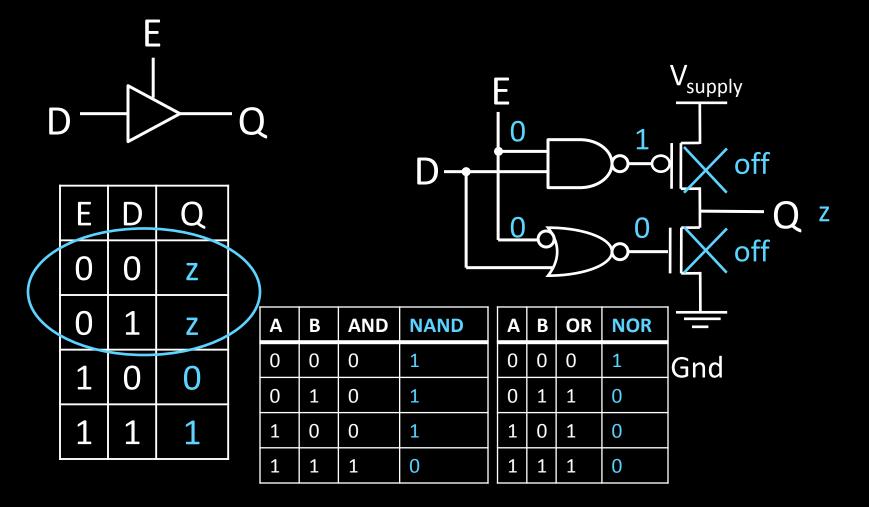
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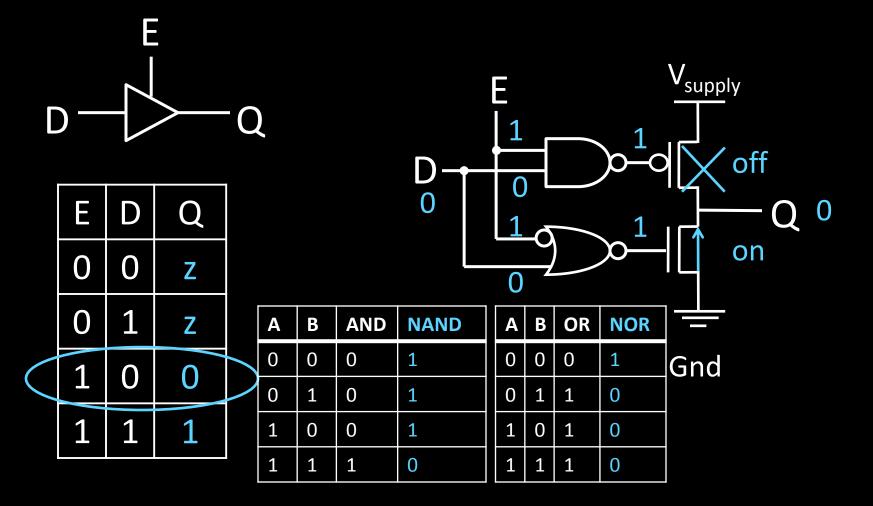
Ε	D	Q
0	0	Z
0	1	Z
1	0	0
1	1	1



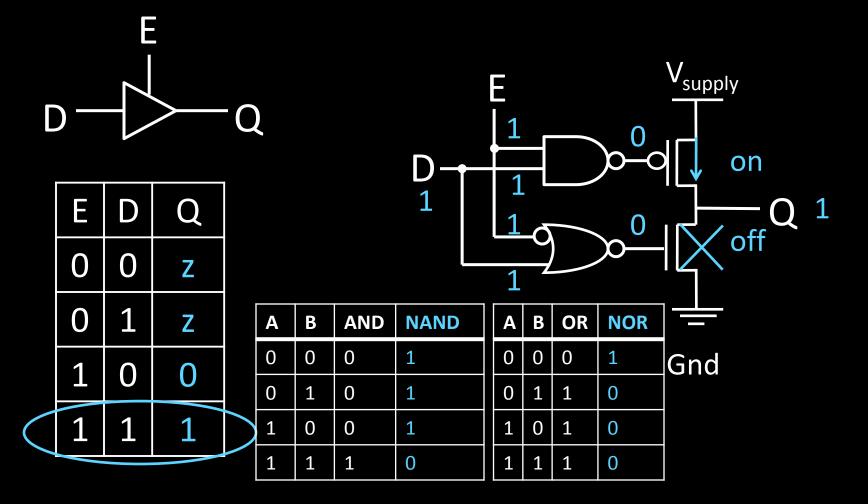
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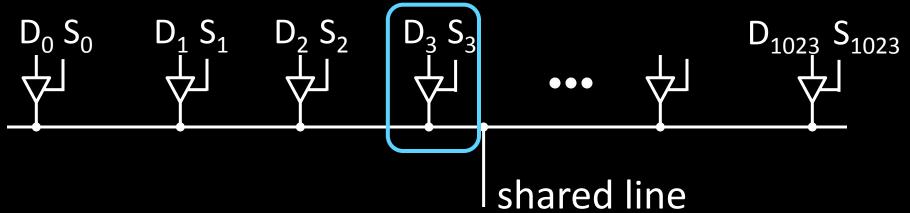
- If enabled (E=1), then Q = D
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- If enabled (E=1), then Q = D
- Otherwise, Q is not connected (z = high impedance)



Shared Bus



Takeway

Register files are very fast storage (only a few gate delays), but does not scale to large memory sizes.

Tri-state Buffers allow scaling since multiple registers can be connected to a single output, while only one register actually drives the output.

Goals for today

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- CPU: Register Files (i.e. Memory w/in the CPU)
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- Cache: SRAM (Static RAM—random access memory)
- Memory: DRAM (Dynamic RAM)

Next Goal

How do we build large memories?

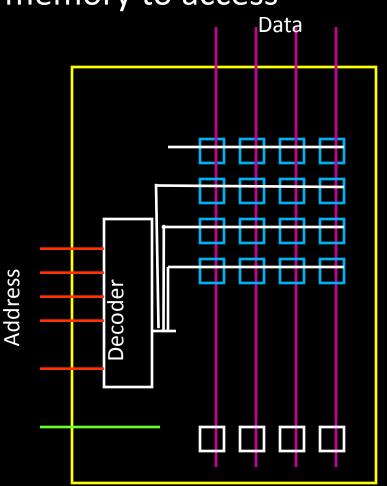
Use similar designs as Tri-state Buffers to connect multiple registers to output line. Only one register will drive output line.

Static RAM (SRAM)—Static Random Access Memory

- Essentially just D-Latches plus Tri-State Buffers
- A decoder selects which line of memory to access

(i.e. word line)

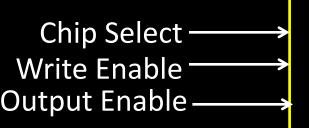
- A R/W selector determines the type of access
- That line is then coupled to the data lines



Static RAM (SRAM)—Static Random Access Memory

- Essentially just D-Latches plus Tri-State Buffers
- A decoder selects which line of memory to access (i.e. word line)
- A R/W selector determines the 22
 type of access

 Address
- That line is then coupled to the data lines



SRAM 4M x 8



E.g. How do we design a 4 x 2 SRAM Module?

(i.e. 4 word lines that are each 2 bits wide)?

2 Address \

4 x 2 SRAM

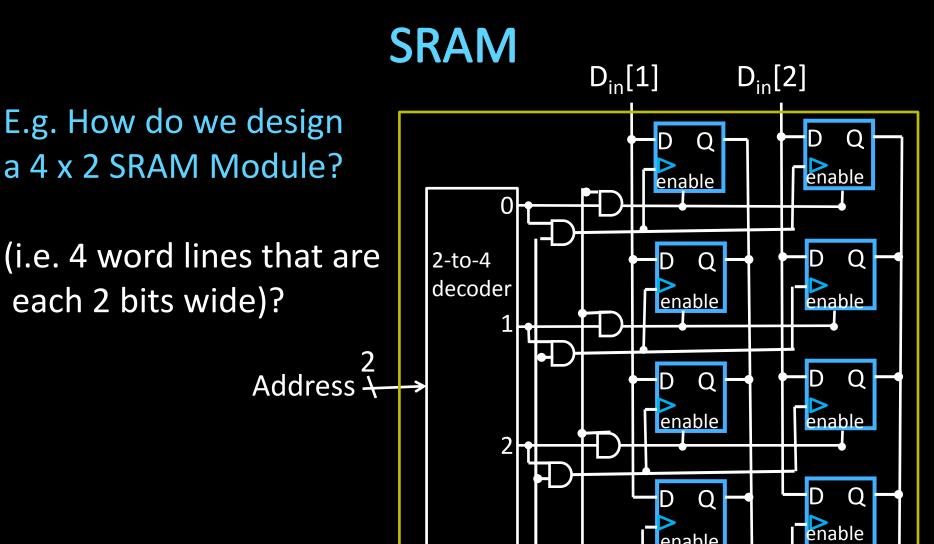
 $D_{in}[1]$

Write Enable — Output Enable —

 $D_{out}^{I}[1]$

 $D_{in}[2]$

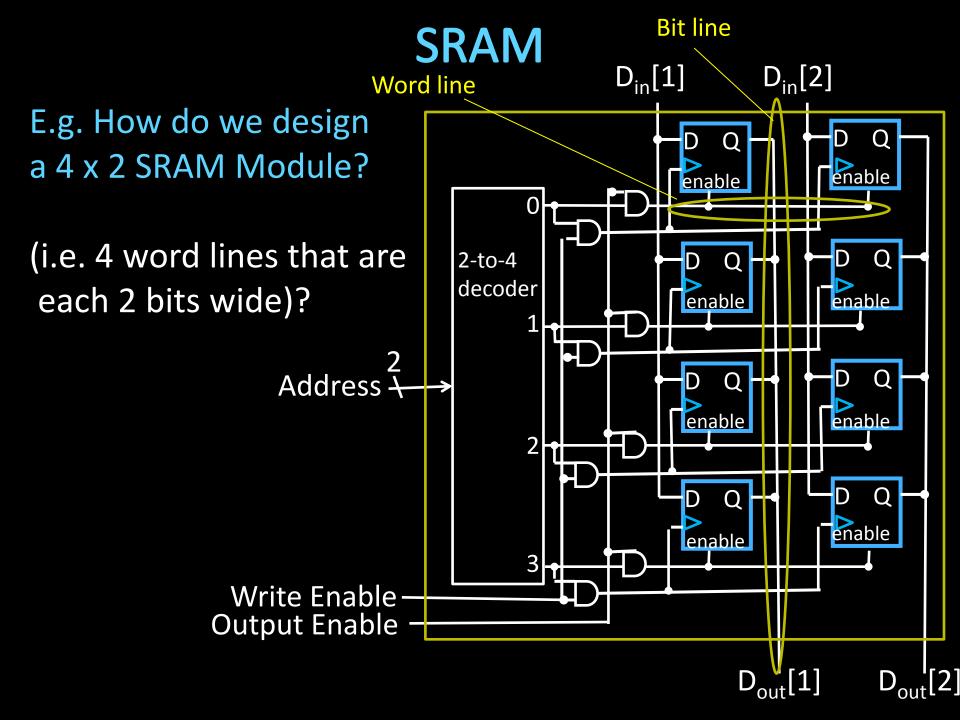
 $D_{out}[2]$

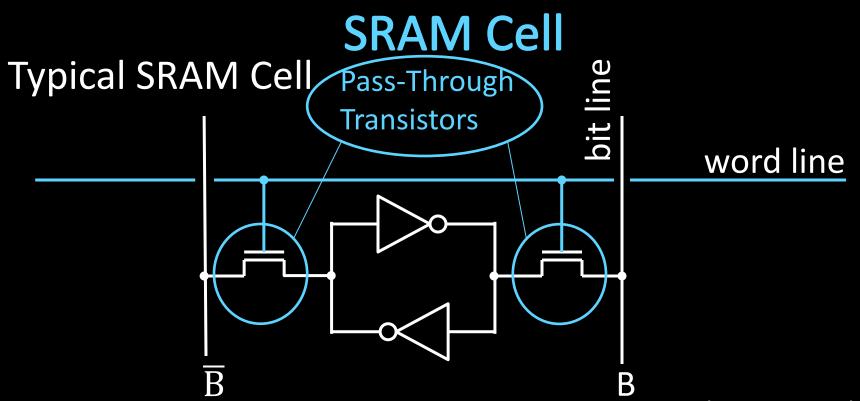


enable

Write Enable-**Output Enable**

each 2 bits wide)?

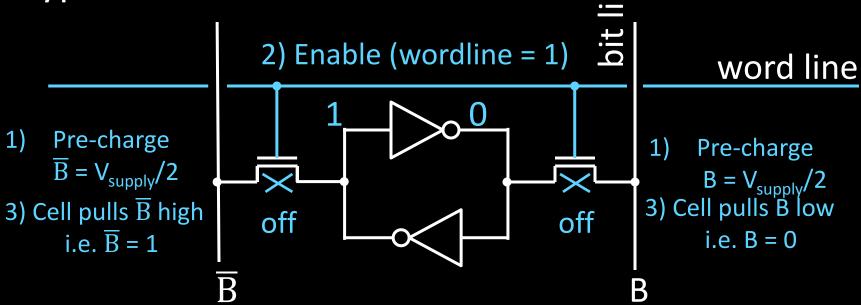




Each cell stores one bit, and requires 4 – 8 transistors (6 is typical)

SRAM Cell

Typical SRAM Cell



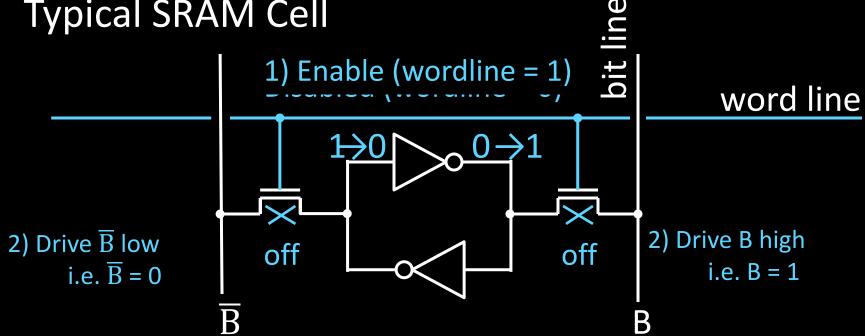
Each cell stores one bit, and requires 4 – 8 transistors (6 is typical)

Read:

- pre-charge B and \overline{B} to $V_{\text{supply}}/2$
- pull word line high
- cell pulls B or \overline{B} low, sense amp detects voltage difference

SRAM Cell

Typical SRAM Cell



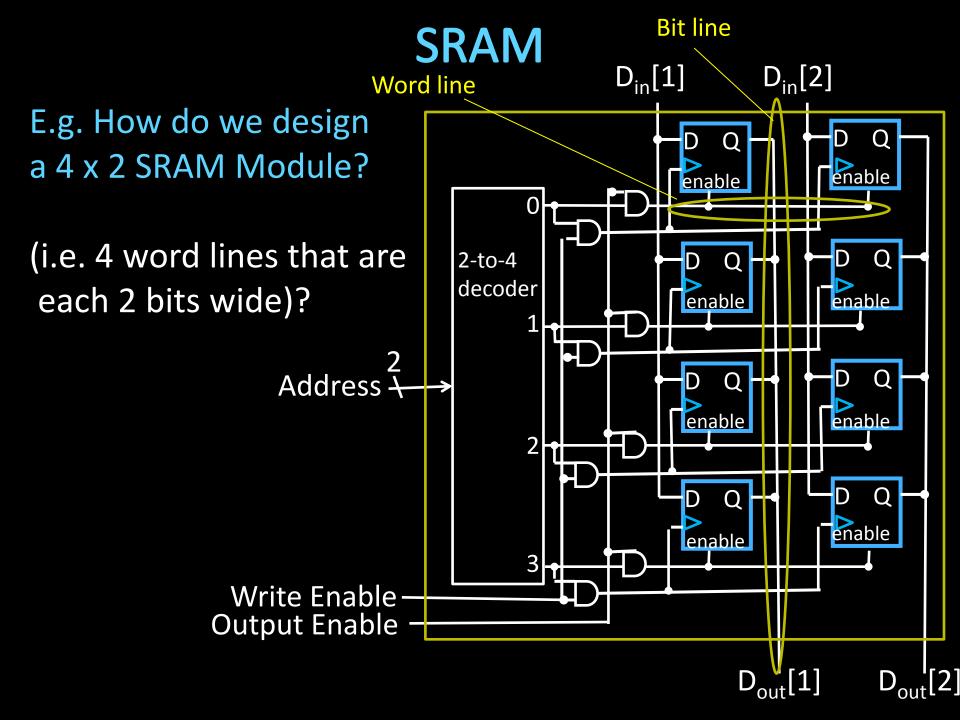
Each cell stores one bit, and requires 4 – 8 transistors (6 is typical)

Read:

- pre-charge B and \overline{B} to $V_{\text{supply}}/2$
- pull word line high
- cell pulls B or B low, sense amp detects voltage difference

Write:

- pull word line high
- drive B and \overline{B} to flip cell





E.g. How do we design a 4 x 2 SRAM Module?

(i.e. 4 word lines that are each 2 bits wide)?

2 Address \

4 x 2 SRAM

 $D_{in}[1]$

Write Enable — Output Enable —

 $D_{out}^{I}[1]$

 $D_{in}[2]$

 $D_{out}[2$

 $D_{in} \downarrow 8$

E.g. How do we design a **4M** x **8** SRAM Module?

(i.e. 4M word lines that are each 8 bits wide)?

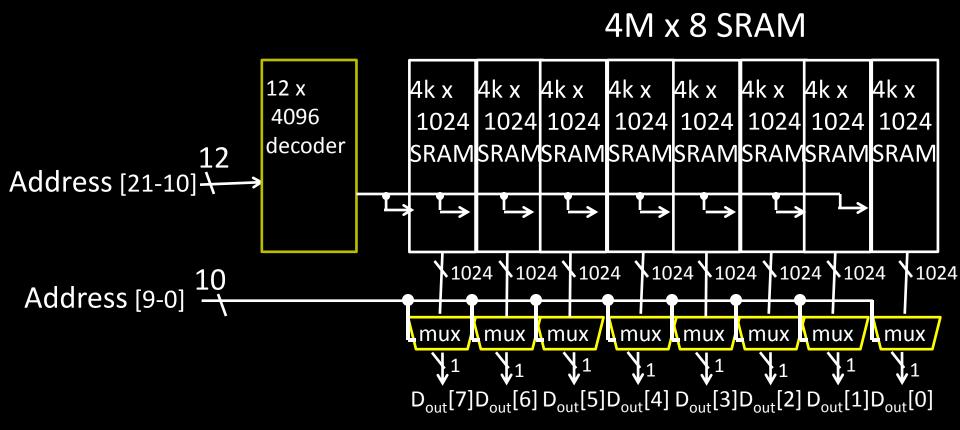
22 Address \

4M x 8 SRAM

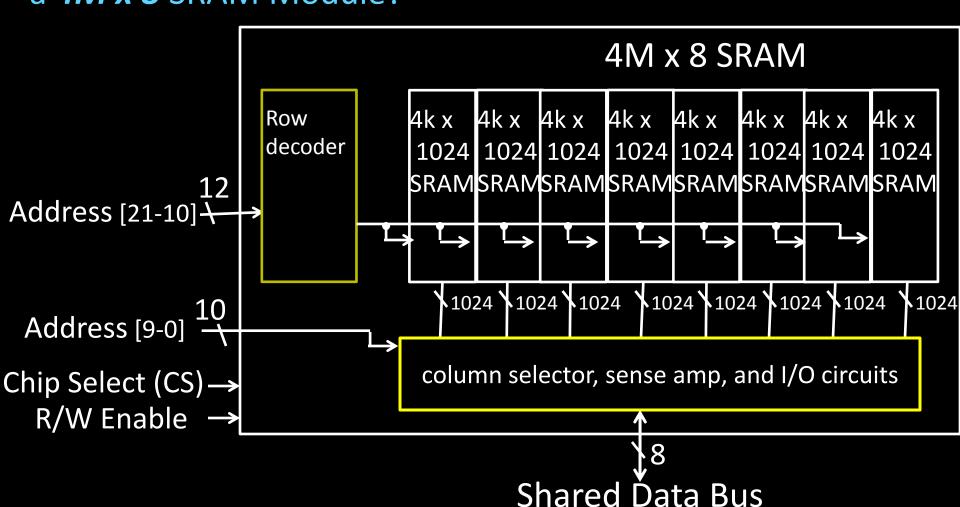
Chip Select

Write Enable — Output Enable —

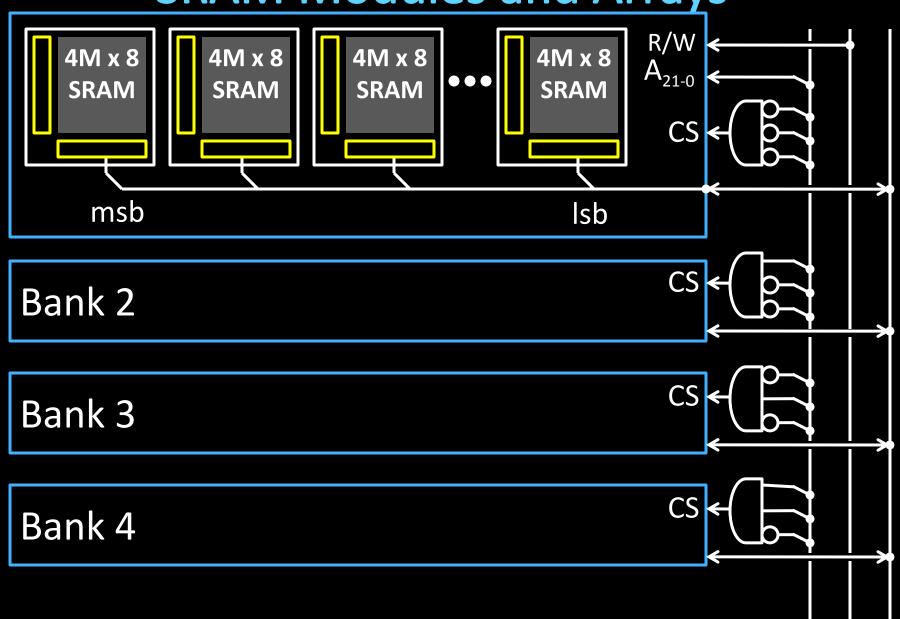
E.g. How do we design a **4M** x **8** SRAM Module?



E.g. How do we design a **4M** x **8** SRAM Module?



SRAM Modules and Arrays



SRAM Summary

SRAM

- A few transistors (~6) per cell
- Used for working memory (caches)

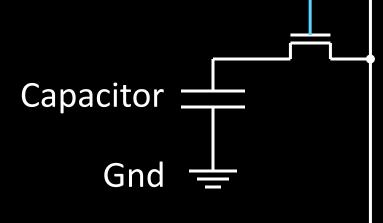
But for even higher density...

Dynamic RAM: DRAM

Dynamic-RAM (DRAM)

Data values require constant refresh

word line



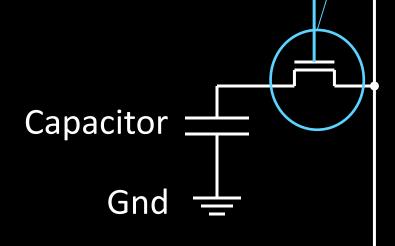
Each cell stores one bit, and requires 1 transistors

Dynamic RAM: DRAM

Dynamic-RAM (DRAM) Transistors

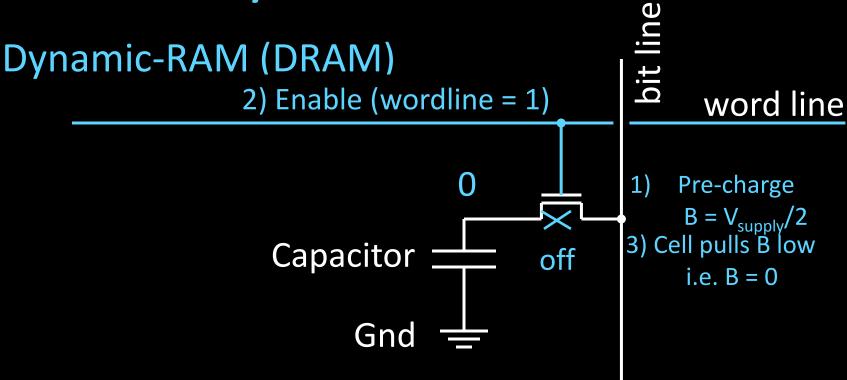
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word line



Each cell stores one bit, and requires 1 transistors

Dynamic RAM: DRAM



Each cell stores one bit, and requires 1 transistors

Read:

- pre-charge B and \overline{B} to $V_{\text{supply}}/2$
- pull word line high
- cell pulls B low, sense amp detects voltage difference

Dynamic RAM: DRAM Dynamic-RAM (DRAM) 1) Enable (wordline = 1) word line 2) Drive B high Capacitor i.e. B = 1Charges capacitor Gnd Each cell stores one bit, and requires 4 – 8 transistors (6 is typical)

Read:

- pre-charge B and \overline{B} to $V_{\text{supply}}/2$
- pull word line high
- ullet cell pulls B or $\overline{
 m B}$ low, sense amp detects voltage difference

Write:

- pull word line high
- drive B charges capacitor

DRAM vs. SRAM

Single transistor vs. many gates

- Denser, cheaper (\$30/1GB vs. \$30/2MB)
- But more complicated, and has analog sensing

Also needs refresh

- Read and write back...
- …every few milliseconds
- Organized in 2D grid, so can do rows at a time
- Chip can do refresh internally

Hence... slower and energy inefficient

Memory

Register File tradeoffs

- Very fast (a few gate delays for both read and write)
- + Adding extra ports is straightforward
- Expensive, doesn't scale
- Volatile

Volatile Memory alternatives: SRAM, DRAM, ...

- Slower
- + Cheaper, and scales well
- Volatile

Non-Volatile Memory (NV-RAM): Flash, EEPROM, ...

- + Scales well
- Limited lifetime; degrades after 100000 to 1M writes

Summary

We now have enough building blocks to build machines that can perform non-trivial computational tasks

Register File: Tens of words of working memory

SRAM: Millions of words of working memory

DRAM: Billions of words of working memory

NVRAM: long term storage (usb fob, solid state disks, BIOS, ...)

Next time we will build a simple processor!